TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

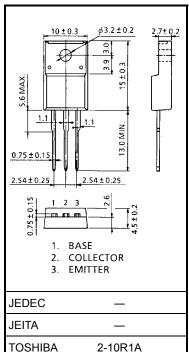
# 2SA1452A

High-Speed, High-Current Switching Applications

- Low collector saturation voltage:  $V_{CE (sat)} = -0.4 V (max) (I_C = -6 A)$
- High-speed switching:  $t_{stg} = 1.0 \ \mu s \ (typ.)$
- Complementary to 2SC3710A

#### Absolute Maximum Ratings (Tc = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-80	V
Collector-emitter voltage	V <sub>CEO</sub>	-80	V
Emitter-base voltage	V <sub>EBO</sub>	-6	V
Collector current	Ι <sub>C</sub>	-12	А
Base current	Ι <sub>Β</sub>	-2	А
Collector power dissipation (Tc = 25°C)	Pc	30	W
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55 to 150	°C



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

temperature, etc.) may cause this product to decrease in the

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

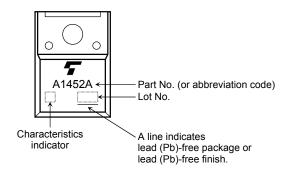
Unit: mm

### **Electrical Characteristics (Tc = 25°C)**

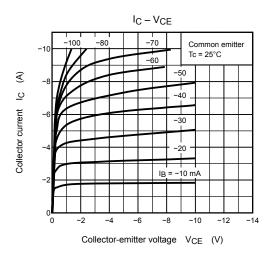
Chara	icteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off c	urrent	I <sub>CBO</sub>	$V_{CB} = -80 V, I_E = 0$	_	—	-10	μA
Emitter cut-off cur	rent	I <sub>EBO</sub>	$V_{EB} = -6 V, I_C = 0$		_	-10	μA
Collector-emitter	breakdown voltage	V (BR) CEO	I <sub>C</sub> = -50 mA, I <sub>B</sub> = 0	-80	_	_	V
DC current gain		h <sub>FE (1)</sub> (Note)	V <sub>CE</sub> = -1 V, I <sub>C</sub> = -1 A	70	_	240	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = -1 V, I <sub>C</sub> = -6 A	40	_	_	
Collector-emitter	saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = -6 A, I <sub>B</sub> = -0.3 A	_	-0.2	-0.4	v
Base-emitter satu	ration voltage	V <sub>BE (sat)</sub>	I <sub>C</sub> = -6 A, I <sub>B</sub> = -0.3 A	_	-0.9	-1.2	v
Transition frequer	су	f <sub>T</sub>	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -1 A	_	50	_	MHz
Collector output c	apacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz	_	400	_	pF
Switching time	Turn-on time	t <sub>on</sub>	20 µs Input <sup>I</sup> B2 Output	_	0.3	_	
	Storage time	t <sub>stg</sub>	$20 \ \mu s \qquad \text{Input} \qquad \boxed{B2} \qquad \qquad$	_	1.0	_	μs
	Fall time	t <sub>f</sub>	∨ <sub>CC</sub> ≈ −30 ∨ −I <sub>B1</sub> = I <sub>B2</sub> = 0.3 A, duty cycle ≤ 1%	_	0.5	_	

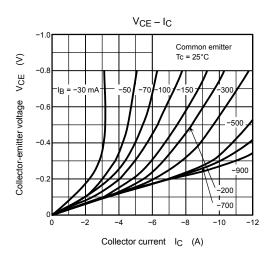
Note: hFE (1) classification O: 70 to 140, Y: 120 to 240

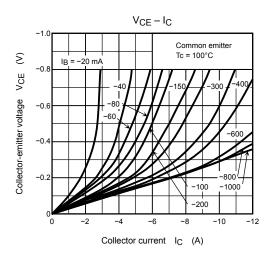
#### Marking

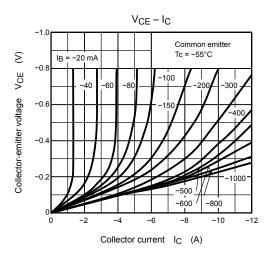


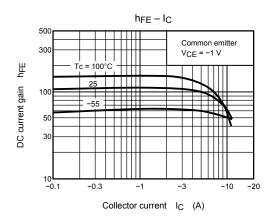
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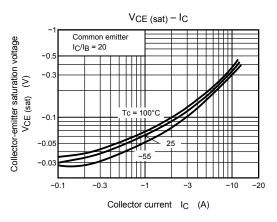




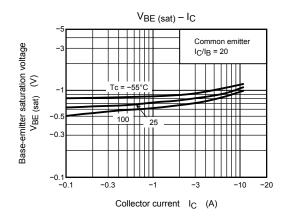


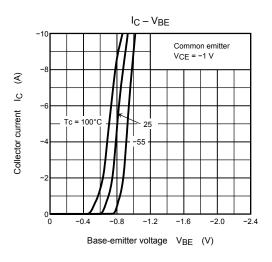


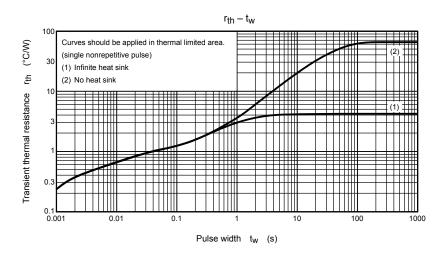


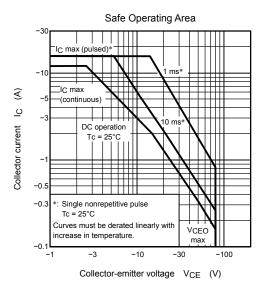


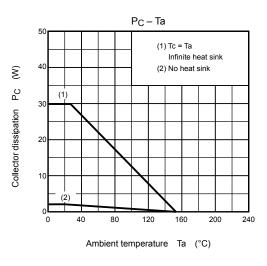
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